

METHOD OF PRODUCING SILICON OXIDE FILM

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Abstract of JP2002363748

PROBLEM TO BE SOLVED: To provide a method of producing a silicon oxide film by which the adverse effect of an oxidizing gas containing oxygen atoms or an inert gas, used together with an organosilicon gas being a gaseous raw material, on a base material can be suppressed at the minimum when the silicon oxide film is deposited by a plasma CVD method. **SOLUTION:** The method of producing the silicon oxide film is characterized in that the vaporization can be carried out in a reaction chamber, the organosilicon gas containing an organosilicon compound having no carbon-silicon bond in the molecule and an oxidizing gas containing oxygen atoms in an amount of not more than 14 moles per mole of the organosilicon compound are used as the gaseous raw material, and the silicon oxide film is deposited to the substrate in the reaction chamber by the plasma CVD method.

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